Descriptions

These N-channel MOSFET are produced using advanced plane MOSFET Technology, which provides Low on-state resistance,high switching performance and excellent quality.These devices are suitable device for SMPS,high Speed switching and general purpose applications.

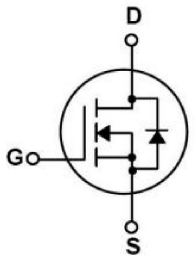
Features

- VDS =600V
- ID = 20A @VGS =10V
- RDS(ON) (Typ)=160mΩ @VGS =10V

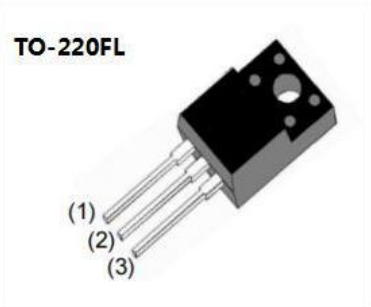
Applications

- Power Supply
- PFC
- High Current, High Speed Switching

Equivalent Circuit



Pinning



PIN1:Gate PIN 2:Drain PIN 3:Source

Marking

Marking	8205

Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25℃)	20	A
Drain Current - Pulsed	I_{DM}	60	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	405	mJ
Avalanche Current	I_{AS}	12.5	A
Power Dissipation	P_D(Tc=25℃)	34	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	℃
Junction-to-Case	$R_{\theta JC}$	3.6	℃/W
Junction-to-Ambient	$R_{\theta JA}$	80	℃/W

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	600			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V V_{GS}=0V T_J=25℃			5.0	μA
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±30V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2.5		4.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=10A		160	190	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_{SD}=1A T_J=25℃			1.2	V
Gate Resistance	R_g	V_{GS} = 0V f = 1.0MHz		3.5		Ω
Input Capacitance	C_{iss}	V_{DS}=100V V_{GS}=0V f=1.0MHz		1725		pF
Output Capacitance	C_{oss}			90		pF
Reverse Transfer Capacitance	C_{rss}			2.5		pF
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=400V I_D=10A R_G=25Ω V_{GS}=10V		26		ns
Turn-On Rise Time	t_r			39		ns
Turn-Off Delay Time	$t_{d(off)}$			115		ns
Turn-Off Fall Time	t_f			32		ns

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Diode Forward Current	I_S			20		A
Total Gate Charge	Q_g	V_{DS}=480V I_D=10A V_{GS}=10V		38.2		nC
Gate-Source Charge	Q_{gs}			10		nC
Gate-Drain Charge	Q_{gd}			13		nC
Reverse recovery time	t_{rr}	V_R=400 V, I_F=10A, dI_F/dt=100 A/μs		141		ns
Reverse recovery charge	Q_{rr}			0.85		uC

Electrical Characteristic Curve

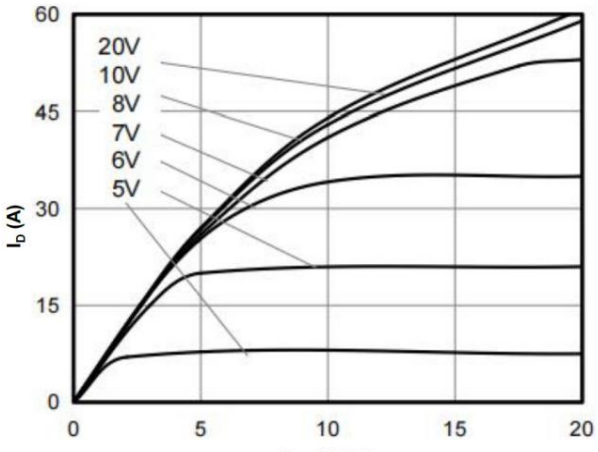


Figure 1: On-Region Characteristics

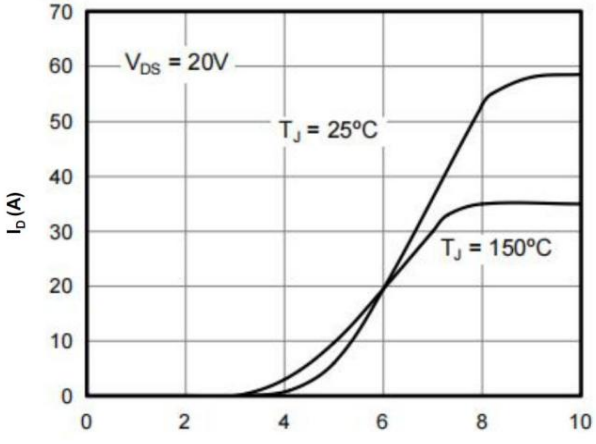


Figure 2: Transfer Characteristics

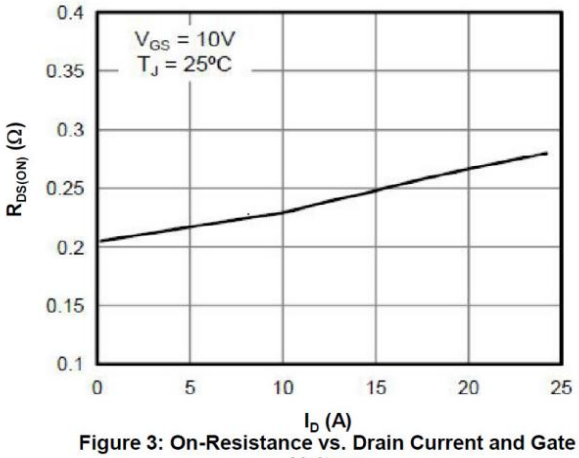


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

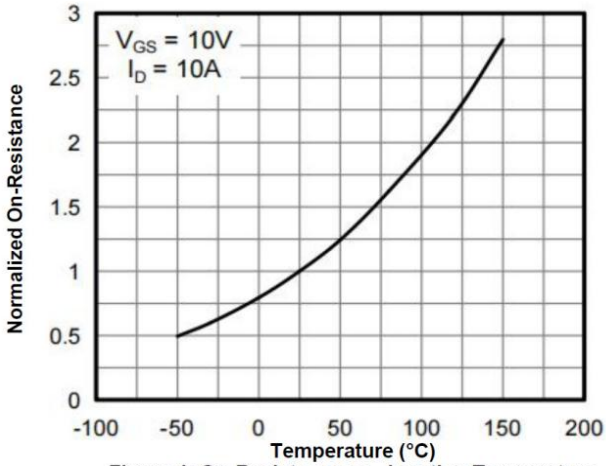


Figure 4: On-Resistance vs. Junction Temperature

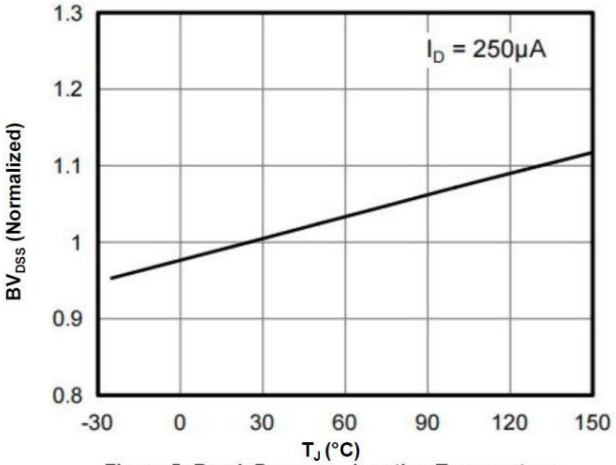


Figure 5: Break Down vs. Junction Temparature

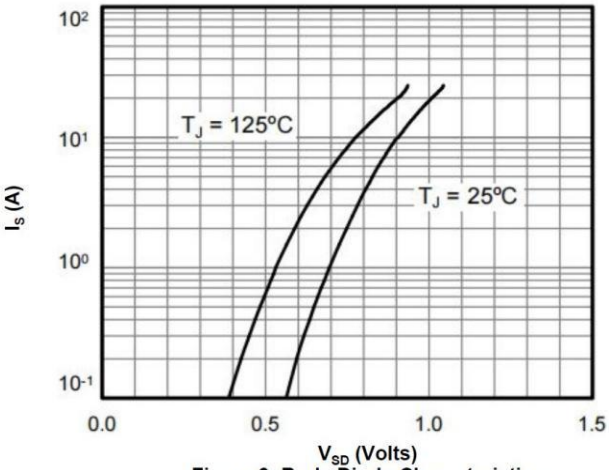


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

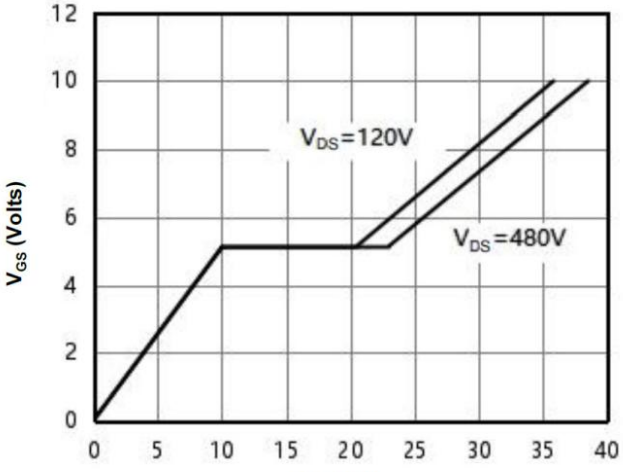


Figure 7: Gate-Charge Characteristics

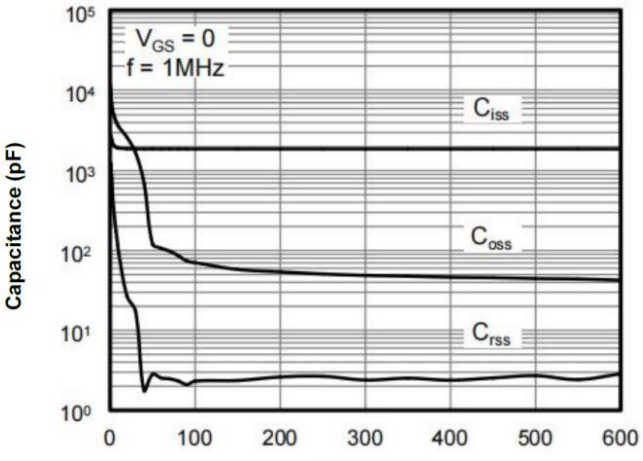


Figure 8: Capacitance Characteristics

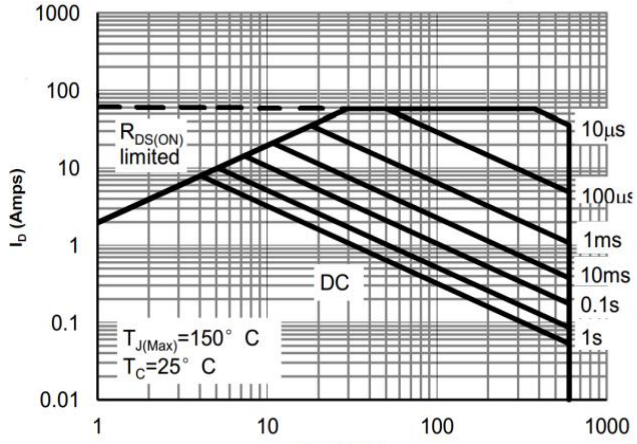


Figure 9: Maximum Forward Biased Safe Operating Area

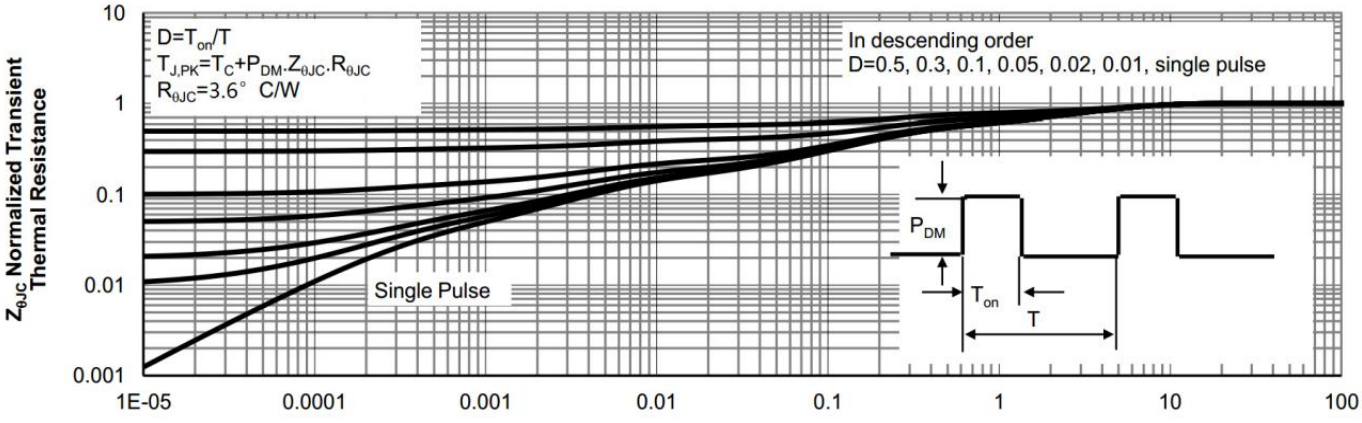
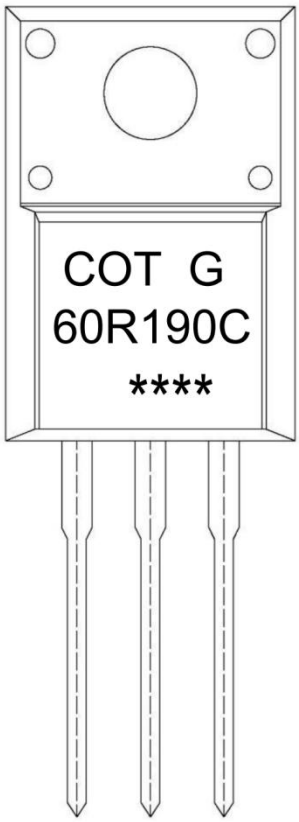


Figure10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT:	Company Logo
G:	Halogen Free
60R190C:	Product Type.
****:	Lot No. Code, code change with Lot No.

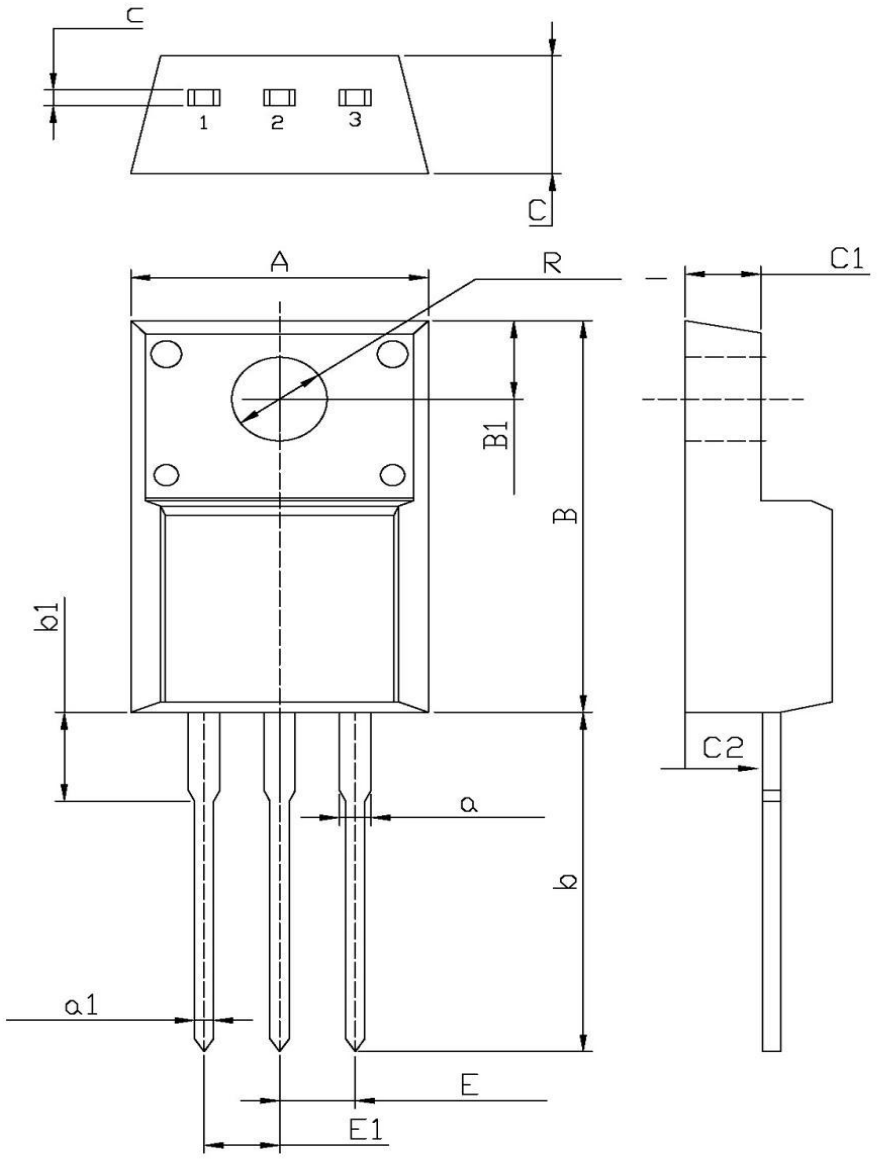
Packaging SPEC.

TUBE INFORMATION

Package Type	Units					Dimension (unit：mm³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-220FL	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

Package Dimensions

TO-220FL 单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.5	4.9	b1	2.90	3.90
c	0.4	0.6	a	1.08	1.48
A	9.96	10.36	a1	0.70	0.90
B	15.67	16.07	E	2.34	2.74
B1	3.30	3.50	E1	2.34	2.74
R	3.08	3.28	C1	2.34	2.74
b	12.48	13.48	C2	2.56	2.96